SN74LV165A 8 位并联负载移位寄存器

1 特性

- V_{CC} 工作电压范围为 2V 至 5.5V
- 5V 时 t_{pd} 最大值为 10.5 ns
- 所有端口上均支持混合模式电压运行
- I_{off} 支持局部关断模式运行
- 闩锁性能超过 250mA，符合 JESD 17 规范

2 应用

增加微控制器上的输入数

3 说明

SN74LV165A 器件是 8 位并行负载移位寄存器，专为 2V 至 5.5V V_{CC} 操作而设计。

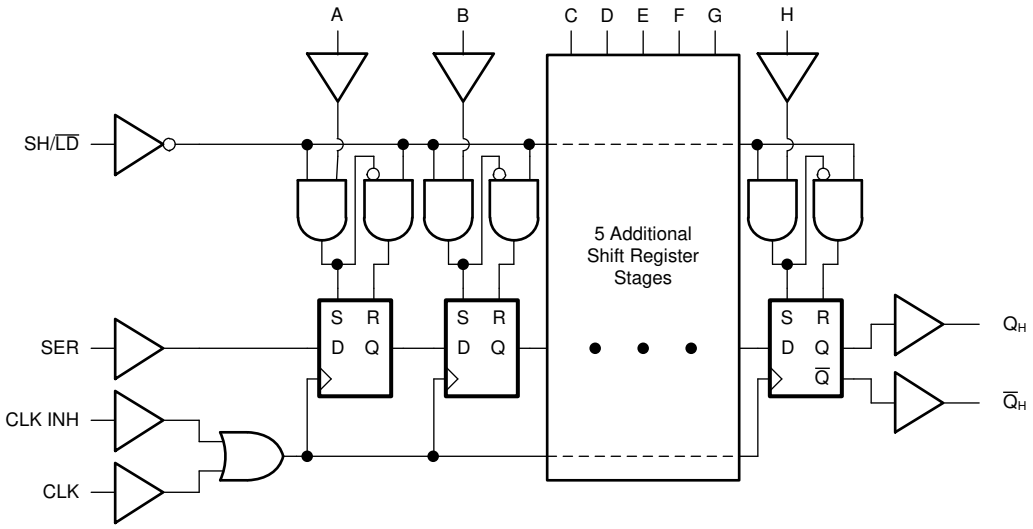
器件计时时，数据通过串行输出 Q_H 传输。当移位/负载 (SH/$\overline{LD}$) 输入为低电平时，可支持八个单独的直接数据输入，从而实现在每个级的并行输入。'LV165A 器件具有时钟抑制功能和补充串行输出 $\overline{Q}_H$。

该器件专用于使用 I_{off} 的局部断电应用。I_{off} 电路会禁用输出，从而在器件断电时防止电流回流损坏器件。

封装信息(1)

器件型号	封装	封装尺寸（标称值）
SN74LV165A	D（SOIC，16）	9.90mm × 3.90mm
	DB（SSOP，16）	6.20mm × 5.30mm
	NS（SO，16）	10.20mm × 5.30mm
	PW（TSSOP，16）	5.00mm × 4.40mm
	DGV（TVSOP，16）	3.60mm × 4.40mm
	RGY（VQFN，16）	4.00mm × 3.50mm
	BQB（WQFN，16）	3.60mm × 2.60mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



逻辑图（正逻辑）

本文档旨在为方便起见，提供有关 TI 产品中文版本的信息，以确认产品的概要。有关适用的官方英文版本的最新信息，请访问 www.ti.com，其内容始终优先。TI 不保证翻译的准确性和有效性。在实际设计之前，请务必参考最新版本的英文版本。

Table of Contents

1 特性 1
2 应用 1
3 说明 1
4 Revision History 2
5 Pin Configuration and Functions 3
6 Specifications 4
6.1 Absolute Maximum Ratings 4
6.2 ESD Ratings 4
6.3 Recommended Operating Conditions 5
6.4 Thermal Information 5
6.5 Electrical Characteristics 6
6.6 Timing Requirements, V_{CC} = 2.5 V ± 0.2 V 6
6.7 Timing Requirements, V_{CC} = 3.3 V ± 0.3 V 6
6.8 Timing Requirements, V_{CC} = 5 V ± 0.5 V 7
6.9 Switching Characteristics, V_{CC} = 2.5 V ± 0.2 V 7
6.10 Switching Characteristics, V_{CC} = 3.3 V ± 0.3 V 7
6.11 Switching Characteristics,V_{CC} = 5 V ± 0.5 V 8
6.12 Timing Diagrams 8
6.13 Operating Characteristics 9
6.14 Typical Characteristics 9
7 Parameter Measurement Information 10
8 Detailed Description 11
8.1 Overview 11
8.2 Functional Block Diagram 11
8.3 Feature Description 11
8.4 Device Functional Modes 13
9 Application and Implementation 14
9.1 Application Information 14
9.2 Typical Application 14
9.3 Power Supply Recommendations 16
9.4 Layout 16
10 Device and Documentation Support 17
10.1 Documentation Support 17
10.2 Receiving Notification of Documentation Updates 17
10.3 支持资源 17
10.4 Trademarks 17
10.5 静电放电警告 17
10.6 术语表 17
11 Mechanical, Packaging, and Orderable Information 17

4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision Q (December 2022) to Revision R (March 2023) — **Page**

- 根据当前标准更新了文档的结构布局和表的格式 1

Changes from Revision P (June 2022) to Revision Q (December 2022) — **Page**

- 将数据表状态从“预告信息”更改为“生产数据” 1

Changes from Revision O (November 2016) to Revision P (June 2022) — **Page**

- 向器件信息、引脚配置和热性能信息表中添加了 BQB (WQFN) 封装信息 1
- 更新了整个文档中的表格、图和交叉参考的编号格式 1
- Updated specifications table formatting 6

Changes from Revision N (July 2013) to Revision O (November 2016) — **Page**

- 添加了*应用*部分、*器件信息表*、*目录*、*引脚配置和功能*部分、*规格*部分、*ESD 等级表*、*热性能信息表*、*典型特性*部分、*详细说明*部分、*应用和实现*部分、*电源相关建议*部分、*布局*部分、*器件和文档支持*部分 以及*机械、封装和可订购信息*部分 1

Copyright © 2023 Texas Instruments Incorporated

5 Pin Configuration and Functions

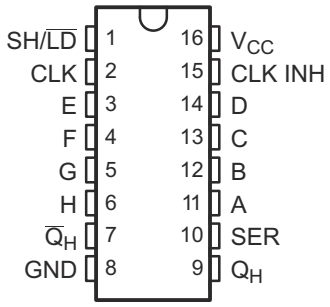


图 5-1. D, DB, DGV, N or PW Package, 16-Pin SOIC, SSOP, TVSOP, SOP or TSSOP (Top View)

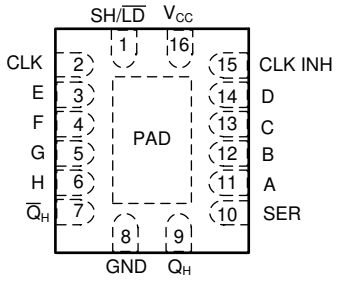


图 5-2. RGY or BQB Package, 16-Pin VQFN or WQFN (Top View)

表 5-1. Pin Functions

PIN		TYPE (1)	DESCRIPTION
NAME	NO.		
A	11	I	Serial input A
B	12	I	Serial input B
C	13	I	Serial input C
CLK	2	I	Storage clock
CLK INH	15	I	Storage clock
D	14	I	Serial input D
E	3	I	Serial input E
F	4	I	Serial input F
G	5	I	Serial input G
GND	8	G	Ground pin
H	6	I	Serial input H
$\overline{Q}_H$	7	O	Output H, inverted
Q_H	9	O	Output H
SH/ $\overline{LD}$	1	I	Load Input
SER	10	I	Serial input
V_{CC}	16	P	Power pin
PAD		—	Thermal Pad(2)

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.
(2) RGY and BQB Package Only

Copyright © 2023 Texas Instruments Incorporated

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		– 0.5	7	V
V_I	Input voltage(2)		– 0.5	7	V
V_O	Voltage range applied to any output in the high-impedance or power-off state(2)		– 0.5	7	V
V_O	Output voltage (2) (3)		– 0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		– 20	mA
I_{OK}	Output clamp current	V_O < 0		– 50	mA
I_O	Continuous output current	V_O = 0 to V_{CC}		±25	mA
	Continuous current through V_{CC} or GND			±50	mA
T_{jmax}	Maximum virtual junction temperature			150	°C
T_{stg}	Storage temperature		– 65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
(3) This value is limited to 5.5 V maximum.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	V
		Machine Model (MM), per JEDEC specification	±200	
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 (2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

Copyright © 2023 Texas Instruments Incorporated

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		V
		V_{CC} = 2.3 V to 2.7 V	V_{CC} × 0.7		
		V_{CC} = 3 V to 3.6 V	V_{CC} × 0.7		
		V_{CC} = 4.5 V to 5.5 V	V_{CC} × 0.7		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5	V
		V_{CC} = 2.3 V to 2.7 V		V_{CC} × 0.3	
		V_{CC} = 3 V to 3.6 V		V_{CC} × 0.3	
		V_{CC} = 4.5 V to 5.5 V		V_{CC} × 0.3	
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		– 50	μA
		V_{CC} = 2.3 V to 2.7 V		– 2	mA
		V_{CC} = 3 V to 3.6 V		– 6	
		V_{CC} = 4.5 V to 5.5 V		– 12	
I_{OL}	Low-level output current	V_{CC} = 2 V		50	μA
		V_{CC} = 2.3 V to 2.7 V		2	mA
		V_{CC} = 3 V to 3.6 V		6	
		V_{CC} = 4.5 V to 5.5 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 2.3 V to 2.7 V		200	ns/V
		V_{CC} = 3 V to 3.6 V		100	
		V_{CC} = 4.5 V to 5.5 V		20	
T_A	Operating free-air temperature		– 40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*

6.4 Thermal Information

THERMAL METRIC(1)		SN74LV165A							UNIT
		D (SOIC)	DB (SSOP)	NS (SO)	PW (TSSOP)	DGV (TVSOP)	RGY (VQFN)	BQB (WQFN)	
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	86.2	102.8	89.4	113.3	125.9	48.8	85.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	46.1	53.3	47.9	48.3	51	46.7	82.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.8	53.5	49.8	58.4	57.7	24.9	55.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	13.2	16.6	16.6	6.4	5.7	2	9.4	°C/W
ψ_{JB}	Junction-to-board characterization parameter	43.5	52.9	49.5	57.8	57.2	24.9	55.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	11.7	33.3	°C/W

(1) For more information about traditional and new thermal metrics, see *Semiconductor and IC Package Thermal Metrics*

Copyright © 2023 Texas Instruments Incorporated

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted).

PARAMETER		TEST CONDITIONS	V_{CC}	– 40°C to 85°C			– 40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	High-level output voltage	I_{OH} = – 50 mA	2 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1			V
		I_{OH} = – 2 mA	2.3 V	2			2			
		I_{OH} = – 6 mA	3 V	2.48			2.48			
		I_{OH} = – 12 mA	4.5 V	3.8			3.8			
V_{OL}	Low-level output voltage	I_{OL} = 50 mA	2 V to 5.5 V			0.1			0.1	V
		I_{OL} = 2 mA	2.3 V			0.4			0.4	
		I_{OL} = 6 mA	3 V			0.44			0.44	
		I_{OL} = 12 mA	4.5 V			0.55			0.55	
I_I	Input leakage current	V_I = 5.5 V or GND	0 V to 5.5 V			±1			±1	µA
I_{CC}	Static supply current	V_I = V_{CC} or GND, I_O = 0	5.5 V			20			20	µA
I_{off}	Partial power down current	V_I or V_O = 0 to 5.5 V	0			5			5	µA
C_i	Input capacitance	V_I = V_{CC} or GND	3.3 V		1.7			1.7		pF

6.6 Timing Requirements, V_{CC} = 2.5 V ± 0.2 V

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER		TEST CONDITION	25°C		– 40°C to 85°C		– 40°C to 125°C		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration	CLK high or low	8.5		9		9		ns
		SH/ $\overline{LD}$ low	11		13		13		
t_{su}	Setup time	SH/ $\overline{LD}$ high before CLK ↑	7		8.5		8.5		ns
		SER before CLK ↑	8.5		9.5		9.5		
		CLK INH before CLK ↑	7		7		7		
		Data before SH/ $\overline{LD}$ ↑	11.5		12		12		
t_h	Hold time	SER data after CLK ↑	-1		0		0		ns
		Parallel data after SH/ $\overline{LD}$ ↑	0		0		0		
		SH/ $\overline{LD}$ high after CLK ↑	0		0		0		

6.7 Timing Requirements, V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range (unless otherwise noted (see 图 7-1)

PARAMETER		TEST CONDITION	25°C		– 40°C to 85°C		– 40°C to 125°C		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration	CLK high or low	6		7		7		ns
		SH/ $\overline{LD}$ low	7.5		9		9		
t_{su}	Setup time	SH/ $\overline{LD}$ high before CLK ↑	5		6		6		ns
		SER before CLK ↑	5		6		6		
		CLK INH before CLK ↑	5		5		5		
		Data before SH/ $\overline{LD}$ ↑	7.5		8.5		8.5		
t_h	Hold time	SER data after CLK ↑	0		0		0		ns
		Parallel data after SH/ $\overline{LD}$ ↑	0.5		0.5		0.5		
		SH/ $\overline{LD}$ high after CLK ↑	0		0		0		

Copyright © 2023 Texas Instruments Incorporated

6.8 Timing Requirements, V_{CC} = 5 V ± 0.5 V

over recommended operating free-air temperature range (unless otherwise noted) (see 图 7-1)

PARAMETER		TEST CONDITION	25°C		−40°C to 85°C		−40°C to 125°C		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration	CLK high or low	4		4		4		ns
		SH/ $\overline{LD}$ low	5		6		6		
t_{su}	Setup time	SH/ $\overline{LD}$ high before CLK ↑	4		4		4		ns
		SER before CLK ↑	4		4		4		
		CLK INH before CLK ↑	3.5		3.5		3.5		
		Data before SH/ $\overline{LD}$ ↑	5		5		5		
t_h	Hold time	SER data after CLK ↑	0.5		0.5		0.5		ns
		Parallel data after SH/ $\overline{LD}$ ↑	1		1		1		
		SH/ $\overline{LD}$ high after CLK ↑	0.5		0.5		0.5		

6.9 Switching Characteristics, V_{CC} = 2.5 V ± 0.2 V

over operating free-air temperature range (unless otherwise noted), (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAP	25°C			−40°C to 85°C			−40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
f_{max}			C_L = 15 pF	50	80		45			45			MHz
			C_L = 50 pF	40	65		35			35			
t_{pd}	CLK	Q_H or $\overline{Q}$	C_L = 15 pF		12.2	19.8	1		22	1		22	ns
	SH/ $\overline{LD}$				13.1	21.5	1		23.5	1		23.5	
	H				12.9	21.7	1		24	1		24	
t_{pd}	CLK	Q_H or $\overline{Q}$	C_L = 50 pF		15.3	23.3	1		26	1		26	ns
	SH/ $\overline{LD}$				16.1	25.1	1		28	1		28	
	H				15.9	25.3	1		28	1		28	

6.10 Switching Characteristics, V_{CC} = 3.3 V ± 0.3 V

over operating free-air temperature range (unless otherwise noted), (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAP	25°C			−40°C to 85°C			−40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
f_{max}			C_L = 15 pF	65	115		55			55			MHz
			C_L = 50 pF	60	90		50			50			
t_{pd}	CLK	Q_H or $\overline{Q}$	C_L = 15 pF		8.6	15.4	1		18	1		18	ns
	SH/ $\overline{LD}$				9.1	15.8	1		18.5	1		18.5	
	H				8.9	14.1	1		16.5	1		16.5	
t_{pd}	CLK	Q_H or $\overline{Q}$	C_L = 50 pF		10.9	14.9	1		16.9	1		16.9	ns
	SH/ $\overline{LD}$				11.3	19.3	1		22	1		22	
	H				11.1	17.6	1		20	1		20	

Copyright © 2023 Texas Instruments Incorporated

6.11 Switching Characteristics, V_{CC} = 5 V ± 0.5 V

over recommended operating free-air temperature range (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAP	25°C			–40°C to 85°C			–40°C to 125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
f_{max}			C_L = 15 pF	110	165		90			90			MHz
			C_L = 50 pF	95	125		85			85			
t_{pd}	CLK	Q_H or $\overline{Q}$	C_L = 15 pF		6	9.9	1		11.5	1		11.5	ns
	SH/ $\overline{LD}$				6	9.9	1		11.5	1		11.5	
	H				6	9.9	1		10.5	1		10.5	
t_{pd}	CLK	Q_H or $\overline{Q}$	C_L = 50 pF		7.7	11.9	1		13.5	1		13.5	ns
	SH/ $\overline{LD}$				7.7	11.9	1		13.5	1		13.5	
	H				7.6	11	1		12.5	1		12.5	

6.12 Timing Diagrams

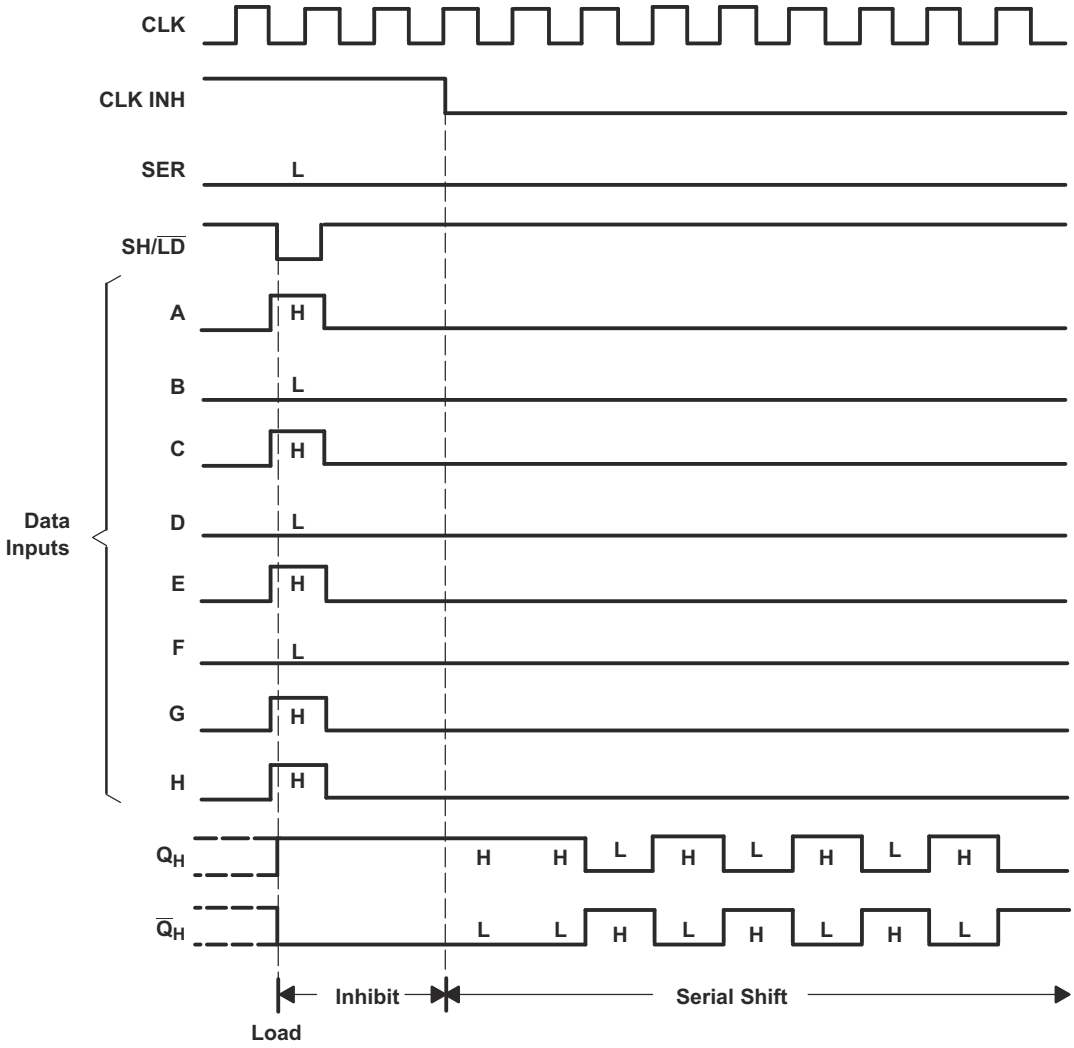


图 6-1. Typical Shift, Load, and Inhibit Sequences

Copyright © 2023 Texas Instruments Incorporated

6.13 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS		V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF	f = 10 MHz	3.3 V	36.1	pF
				5 V	37.5	

6.14 Typical Characteristics

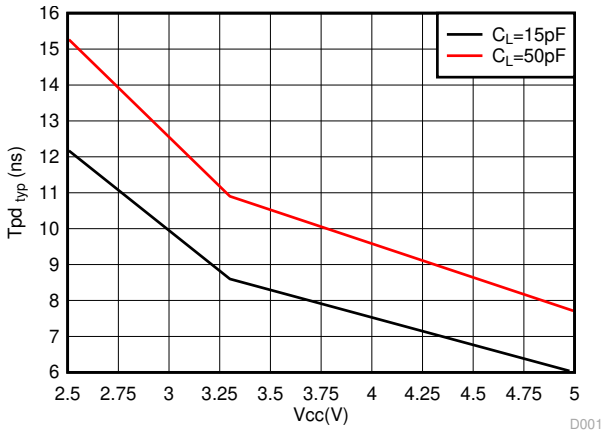
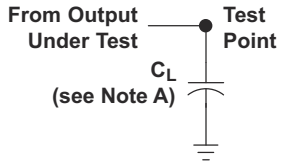
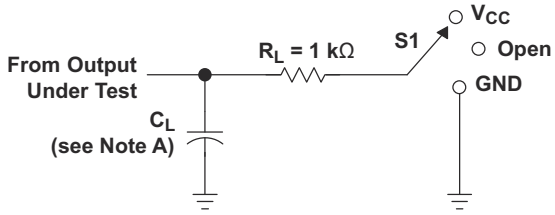


图 6-2. T_{PD} Typical (25°C) vs V_{CC}

7 Parameter Measurement Information

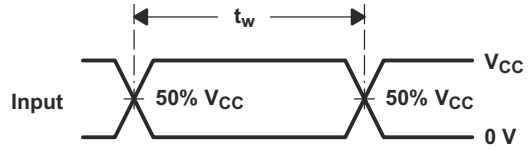


LOAD CIRCUIT FOR
TOTEM-POLE OUTPUTS

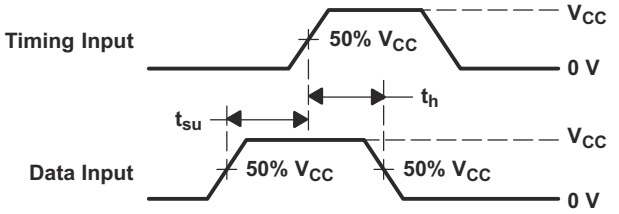


LOAD CIRCUIT FOR
3-STATE AND OPEN-DRAIN OUTPUTS

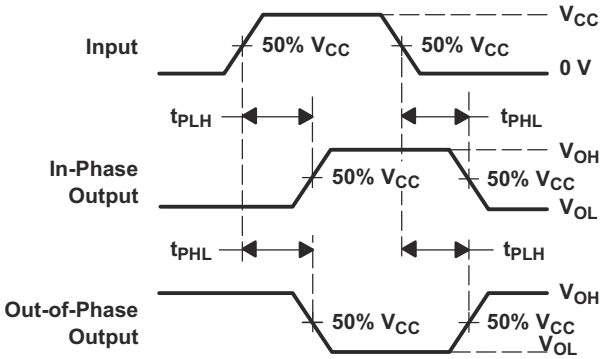
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND
Open Drain	V_{CC}



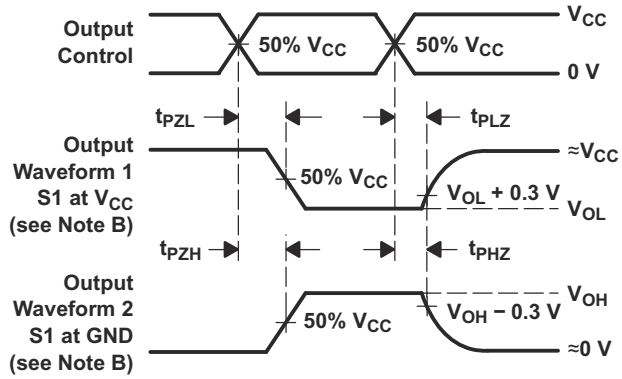
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ⩽ 1 MHz, Z_O = 50 Ω, t_r ⩽ 3 ns, t_f ⩽ 3 ns.
D. The outputs are measured one at a time, with one input transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

图 7-1. Load Circuit and Voltage Waveforms

Copyright © 2023 Texas Instruments Incorporated

8 Detailed Description

8.1 Overview

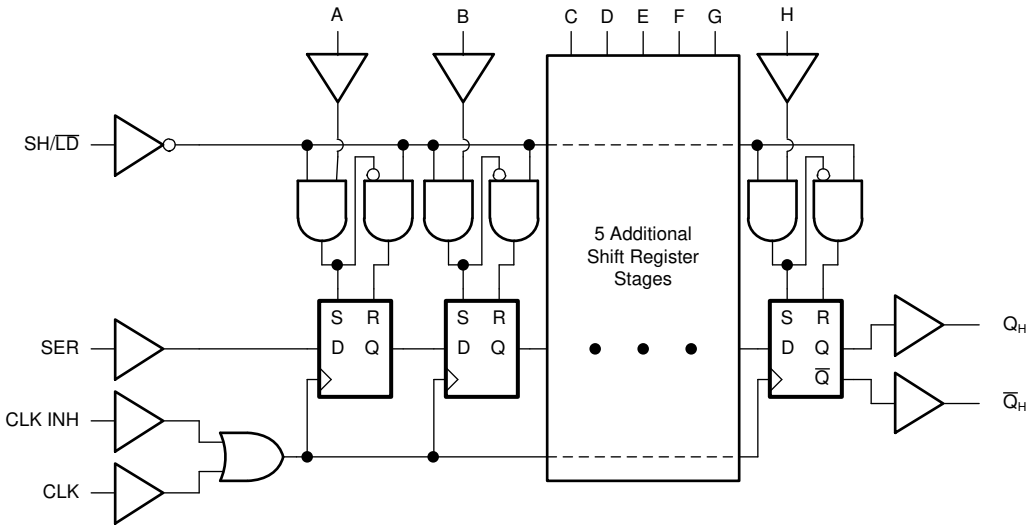
The SN74LV165A device is a parallel-load, 8-bit shift registers designed for 2 V to 5.5 V V_{CC} operation.

When the device is clocked, data is shifted toward the serial output Q_H. Parallel-in access to each stage is provided by eight individual direct data inputs that are enabled by a low level at the shift/load (SH/ $\overline{LD}$) input. The ’ LV165A devices feature a clock-inhibit function and a complemented serial output, $\overline{Q}_H$.

Clocking is accomplished by a low-to-high transition of the clock (CLK) input while SH/ $\overline{LD}$ is held high and clock inhibit (CLK INH) is held low. The functions of CLK and CLK INH are interchangeable. Since a low CLK and a low-to-high transition of CLK INH accomplishes clocking, CLK INH must be changed to the high level only while CLK is high. Parallel loading is inhibited when SH/ $\overline{LD}$ is held high. The parallel inputs to the register are enabled while SH/ $\overline{LD}$ is held low, independently of the levels of CLK, CLK INH, or SER.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.3.2 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

Copyright © 2023 Texas Instruments Incorporated

8.3.3 Partial Power Down (I_{off})

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I_{off} specification in the *Electrical Characteristics* table.

8.3.4 Clamp Diode Structure

图 8-1 shows the inputs and outputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

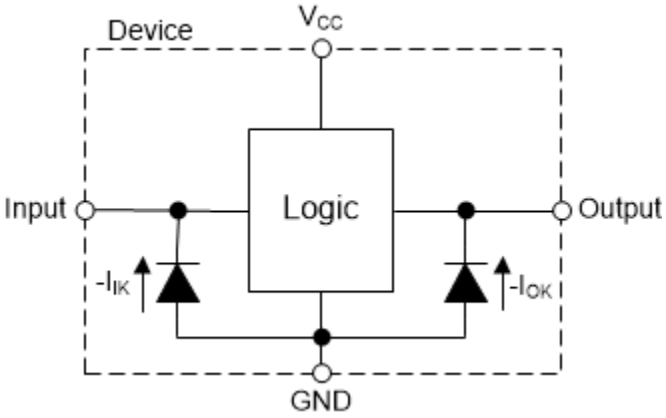


图 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

Copyright © 2023 Texas Instruments Incorporated

8.4 Device Functional Modes

The Operating Mode Table and the Output Function Table list the functional modes of the SN74LV165A.

表 8-1. Operating Mode Table

INPUTS(1)			FUNCTION
SH/$\overline{LD}$	CLK	CLK INH	
L	X	X	Parallel load
H	H	X	No change
H	X	H	No change
H	L	↑	Shift(2)
H	↑	L	Shift(2)

(1) H = High Voltage Level, L = Low Voltage Level, X = Do Not Care, ↑ = Low to High transition
(2) Shift : Content of each internal register shifts towards serial output Q_H. Data at SER is shifted into the first register.

表 8-2. Output Function Table

INTERNAL REGISTERS(1) (2)		OUTPUTS(2)	
A — G	H	Q	$\overline{Q}$
X	L	L	H
X	H	H	L

(1) Internal registers refer to the shift registers inside the device. These values are set by either loading data from the parallel inputs, or by clocking data in from the serial input.
(2) H = High Voltage Level, L = Low Voltage Level, X = Do Not Care

Copyright © 2023 Texas Instruments Incorporated

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

The SN74LV165A is a low drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low-drive and slow-edge rates minimize overshoot and undershoot on the outputs.

9.2 Typical Application

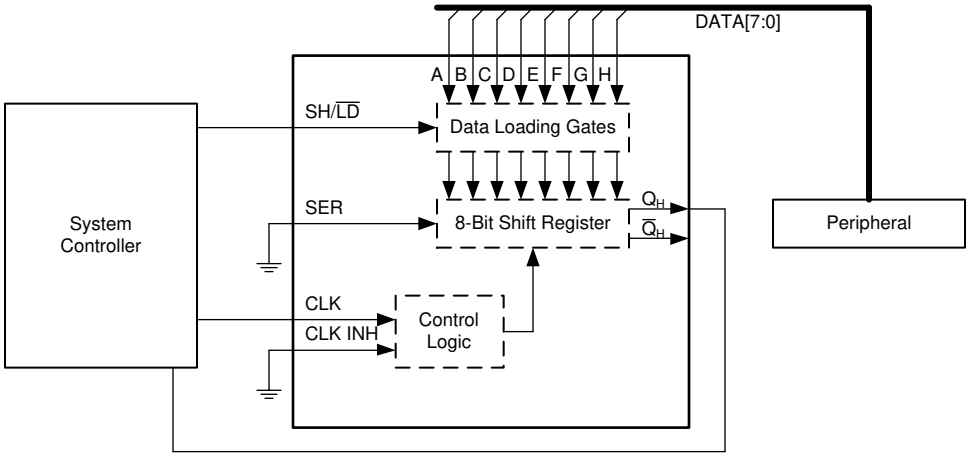


图 9-1. Input Expansion with Shift Registers

9.2.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LV165A plus the maximum static supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LV165A plus the maximum supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74LV165A can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74LV165A can drive a load with total resistance described by $R_L \geqslant V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL}. When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Copyright © 2023 Texas Instruments Incorporated

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices*.

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LV165A (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-kΩ resistor value is often used due to these factors.

The SN74LV165A has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

9.2.4 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is $\leqslant$ 50 pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV165A to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than (V_{CC} / $I_{O(max)}$) Ω. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in MΩ; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

Copyright © 2023 Texas Instruments Incorporated

9.2.5 Application Curve

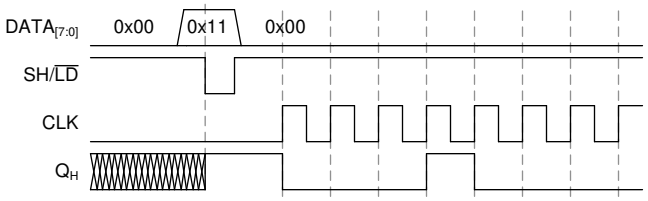


图 9-2. Application Timing Diagram

9.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *节 6.1* section. Each V_{CC} terminal must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends a 0.1-μF capacitor and if there are multiple V_{CC} terminals then TI recommends a 0.01-μF or 0.022-μF capacitor for each power terminal. Multiple bypass capacitors can be paralleled to reject different frequencies of noise. Frequencies of 0.1 μF and 1 μF are commonly used in parallel. The bypass capacitor must be installed as close as possible to the power terminal for best results.

9.4 Layout

9.4.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

9.4.2 Layout Example

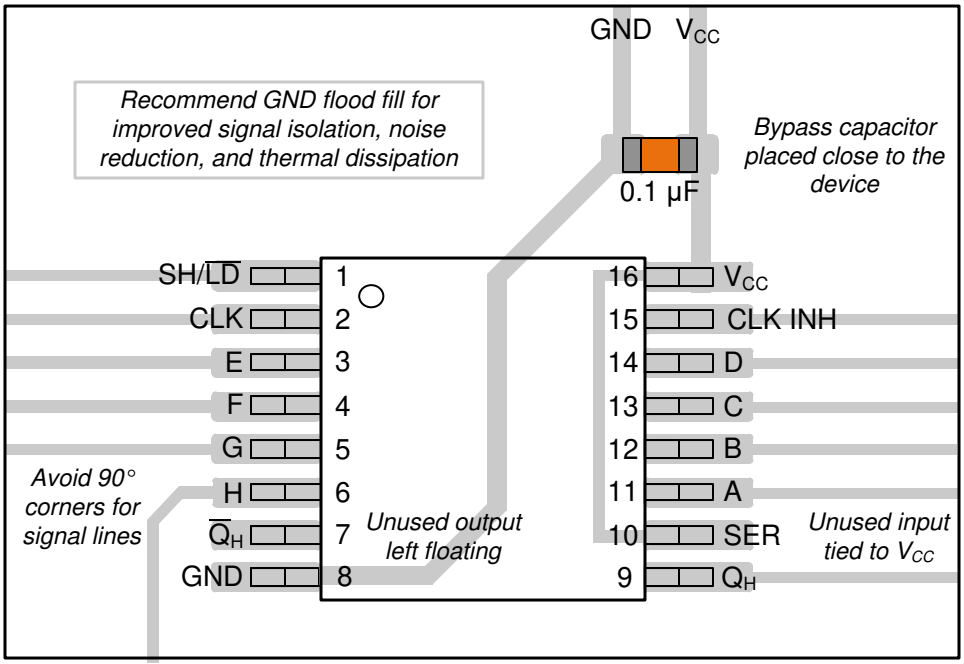


图 9-3. Example Layout for the SN74LV165A in the PW Package

Copyright © 2023 Texas Instruments Incorporated

10 Device and Documentation Support

10.1 Documentation Support

10.1.1 Related Documentation

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

表 10-1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN74LV165A	Click here	Click here	Click here	Click here	Click here

10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates—including silicon errata—go to the product folder for your device on ti.com. In the upper right-hand corner, click the *Alert me* button. This registers you to receive a weekly digest of product information that has changed (if any). For change details, check the revision history of any revised document.

10.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

10.5 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

10.6 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Copyright © 2023 Texas Instruments Incorporated

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74LV165ABQBR	Active	Production	WQFN (BQB) | 16	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ABQBR.A	Active	Production	WQFN (BQB) | 16	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165AD	Obsolete	Production	SOIC (D) | 16	-	-	Call TI	Call TI	-40 to 125	LV165A
SN74LV165ADBR	Active	Production	SSOP (DB) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ADBR.A	Active	Production	SSOP (DB) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ADGVR	Active	Production	TVSOP (DGV) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ADGVR.A	Active	Production	TVSOP (DGV) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ADR	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ADR.A	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ADRG3	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ADRG3.A	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ADRG4	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ADRG4.A	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ANSR	Active	Production	SOP (NS) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	74LV165A
SN74LV165ANSR.A	Active	Production	SOP (NS) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	74LV165A
SN74LV165APW	Obsolete	Production	TSSOP (PW) | 16	-	-	Call TI	Call TI	-40 to 125	LV165A
SN74LV165APWR	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165APWR.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165APWRG3	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165APWRG3.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165APWRG4	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165APWRG4.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ARGYR	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ARGYR.A	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A
SN74LV165ARGYRG4	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV165A

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LV165A :

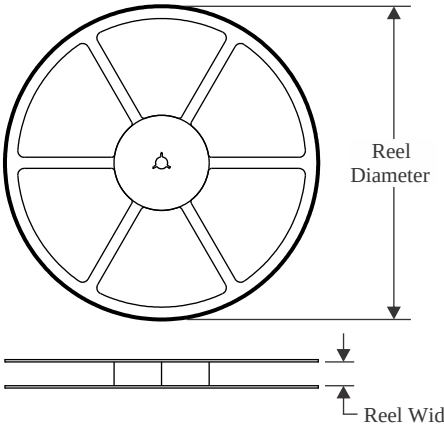
- Automotive : SN74LV165A-Q1
- Enhanced Product : SN74LV165A-EP

NOTE: Qualified Version Definitions:

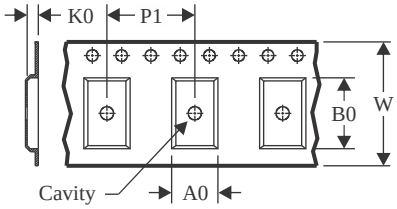
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS

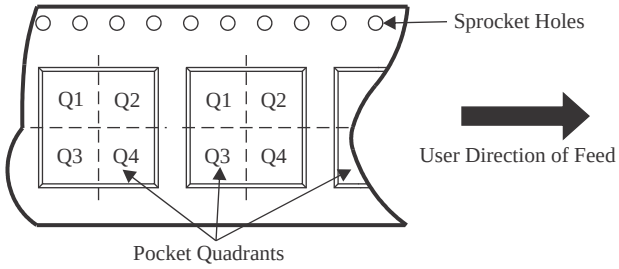


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

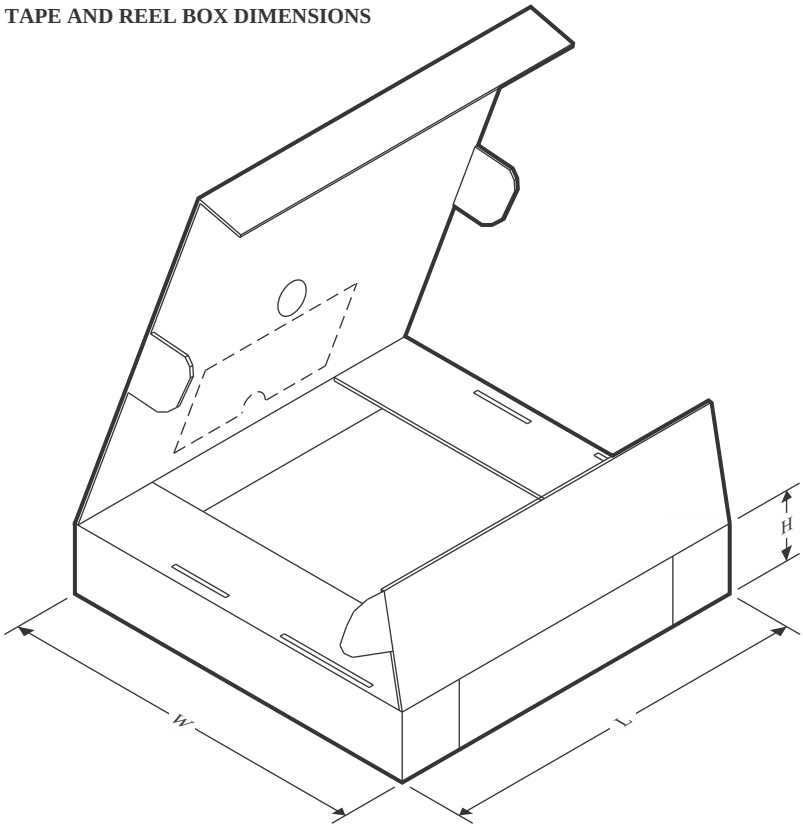
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

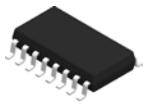
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV165ABQBR	WQFN	BQB	16	3000	180.0	12.4	2.8	3.8	1.2	4.0	12.0	Q1
SN74LV165ADBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN74LV165ADGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74LV165ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74LV165ADRG3	SOIC	D	16	2500	330.0	16.8	6.5	10.3	2.1	8.0	16.0	Q1
SN74LV165ADRG4	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74LV165ANSR	SOP	NS	16	2000	330.0	16.4	8.1	10.4	2.5	12.0	16.0	Q1
SN74LV165APWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV165APWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.3	1.6	8.0	12.0	Q1
SN74LV165APWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV165APWRG3	TSSOP	PW	16	2000	330.0	12.4	6.85	5.45	1.6	8.0	12.0	Q1
SN74LV165APWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV165APWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV165APWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.3	1.6	8.0	12.0	Q1
SN74LV165ARGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV165ABQBR	WQFN	BQB	16	3000	210.0	185.0	35.0
SN74LV165ADBR	SSOP	DB	16	2000	353.0	353.0	32.0
SN74LV165ADGVR	TVSOP	DGV	16	2000	353.0	353.0	32.0
SN74LV165ADR	SOIC	D	16	2500	353.0	353.0	32.0
SN74LV165ADRG3	SOIC	D	16	2500	364.0	364.0	27.0
SN74LV165ADRG4	SOIC	D	16	2500	340.5	336.1	32.0
SN74LV165ANSR	SOP	NS	16	2000	353.0	353.0	32.0
SN74LV165APWR	TSSOP	PW	16	2000	353.0	353.0	32.0
SN74LV165APWR	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74LV165APWR	TSSOP	PW	16	2000	356.0	356.0	35.0
SN74LV165APWRG3	TSSOP	PW	16	2000	366.0	364.0	50.0
SN74LV165APWRG4	TSSOP	PW	16	2000	353.0	353.0	32.0
SN74LV165APWRG4	TSSOP	PW	16	2000	353.0	353.0	32.0
SN74LV165APWRG4	TSSOP	PW	16	2000	367.0	367.0	35.0
SN74LV165ARGYR	VQFN	RGY	16	3000	360.0	360.0	36.0

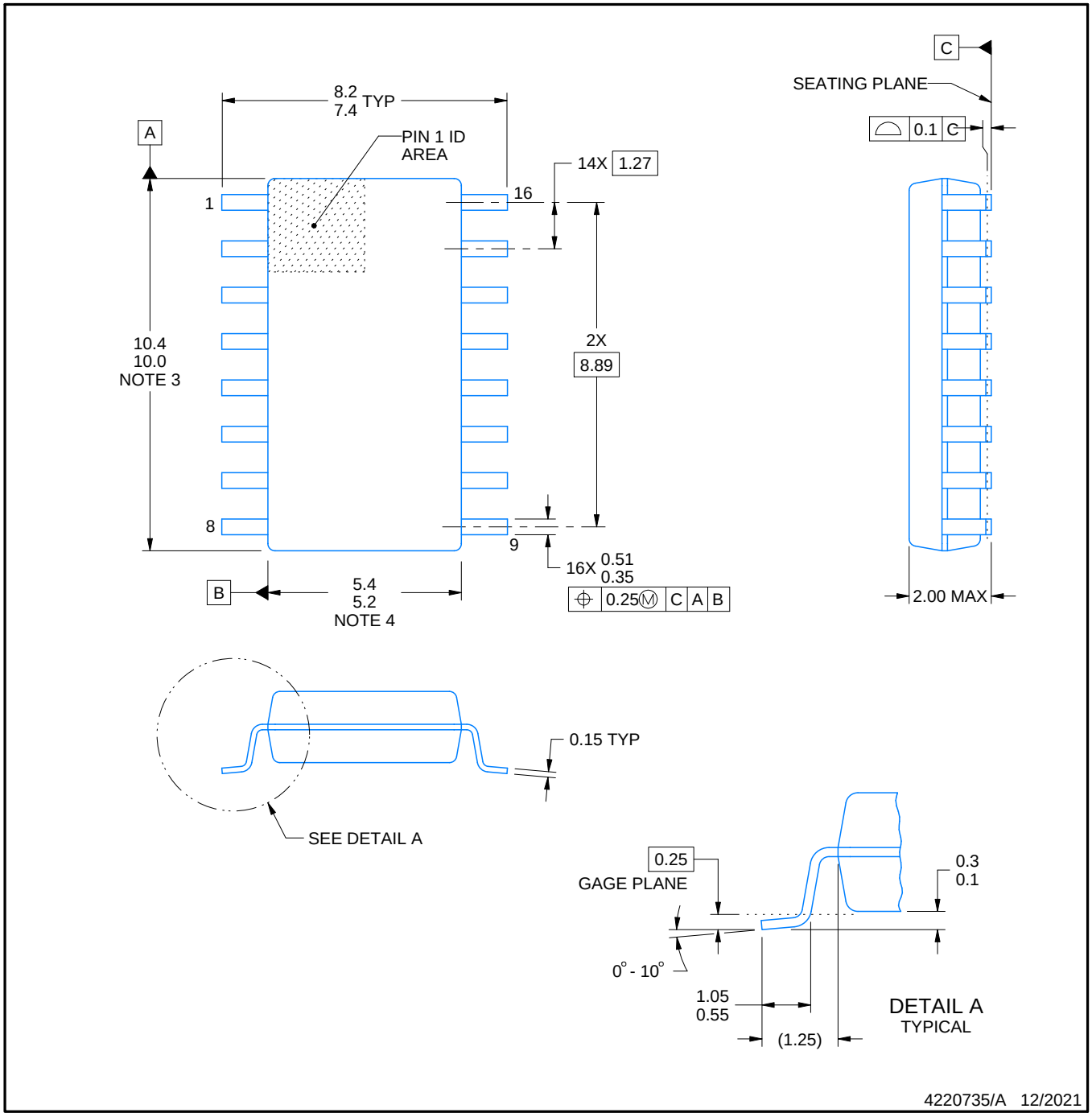


PACKAGE OUTLINE

NS0016A

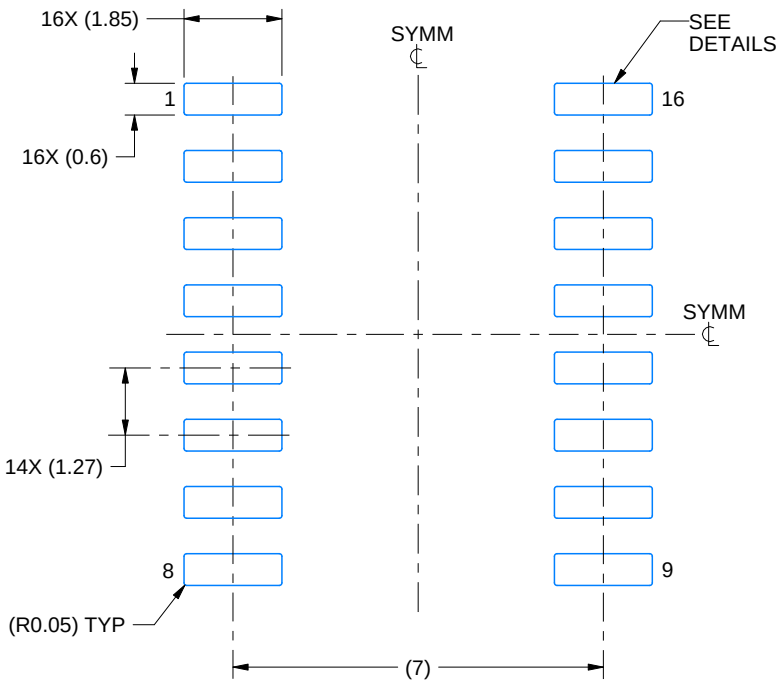
SOP - 2.00 mm max height

SOP

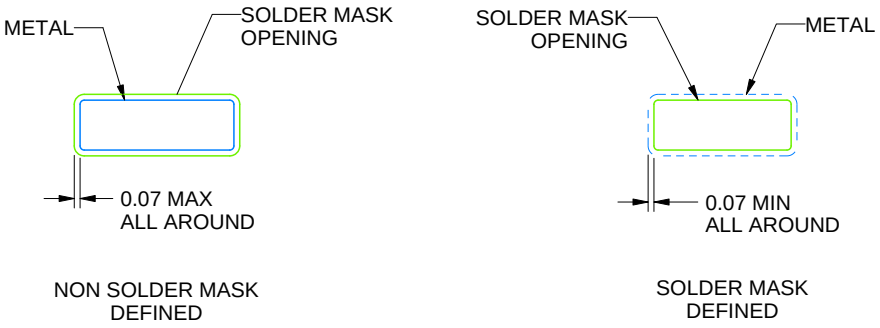


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.



LAND PATTERN EXAMPLE
SCALE:7X



NON SOLDER MASK
DEFINED

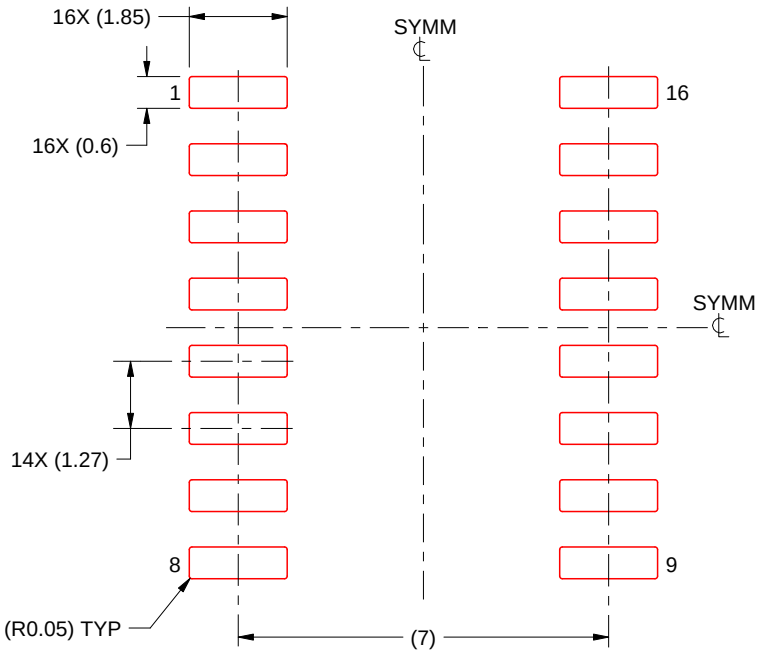
SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4220735/A 12/2021

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:7X

4220735/A 12/2021

NOTES: (continued)

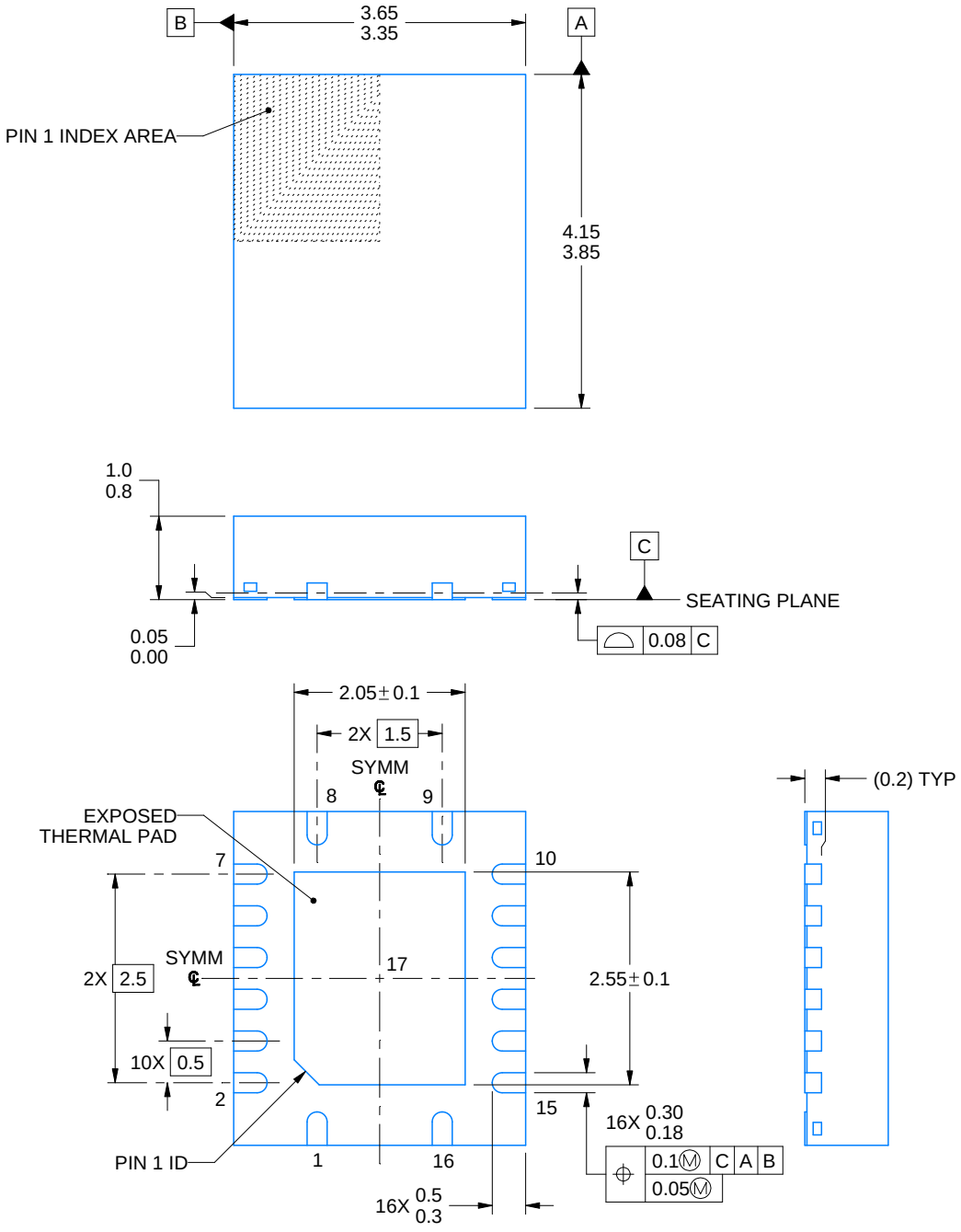
7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

RGY0016A

PACKAGE OUTLINE

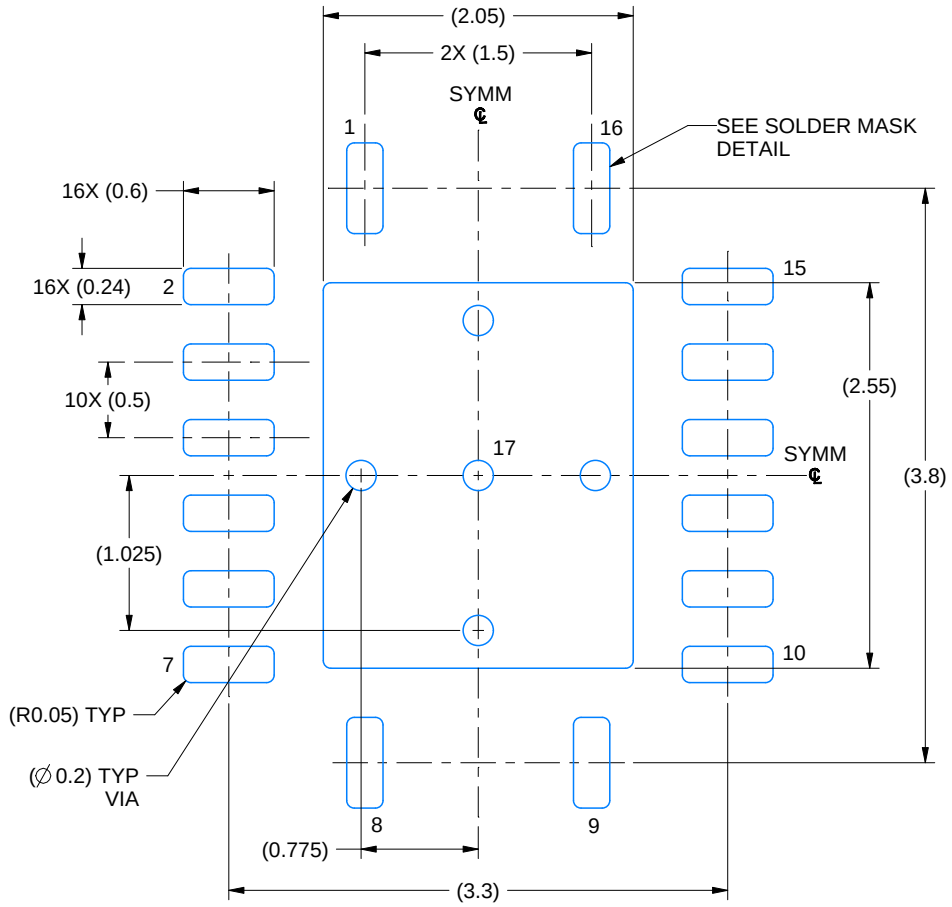
VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

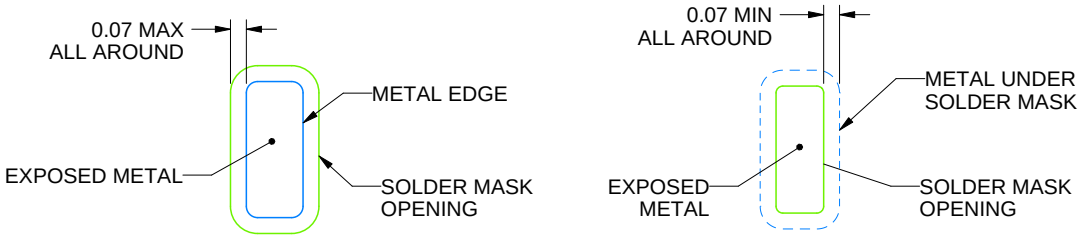


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

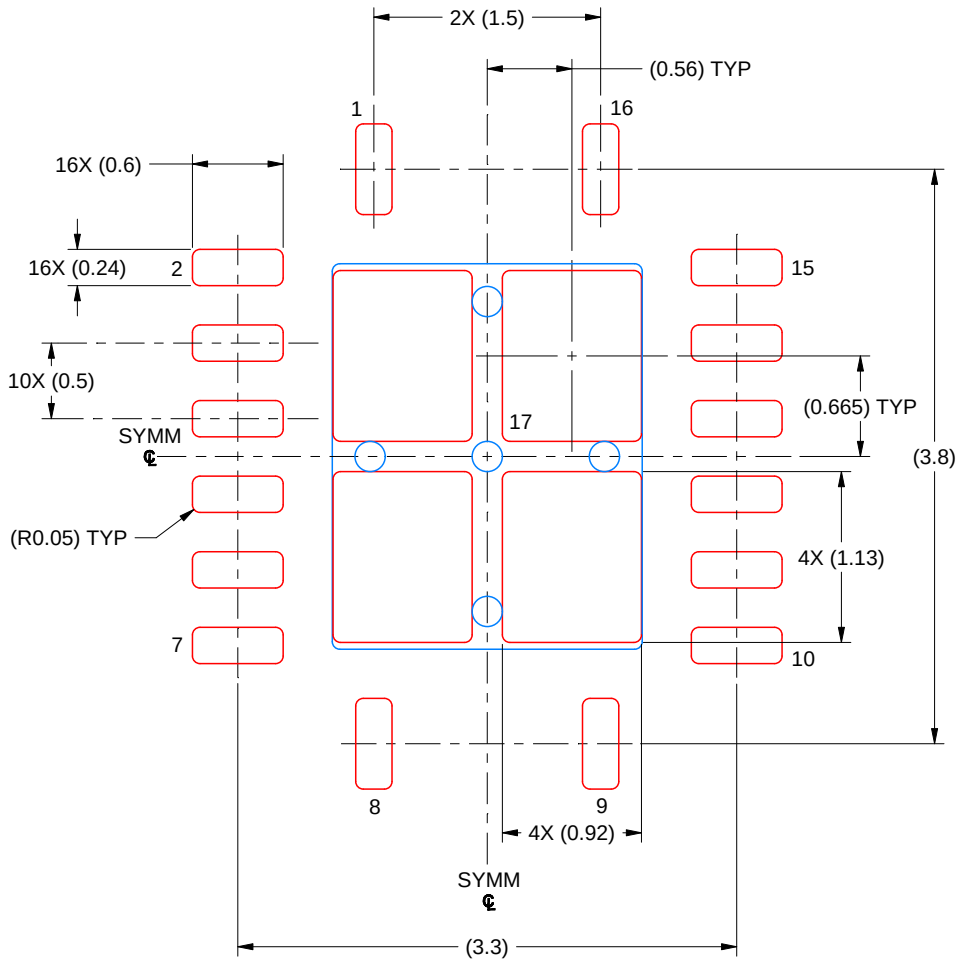


SOLDER MASK DETAILS

4225140/A 07/2019

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 MM THICK STENCIL
SCALE: 20X

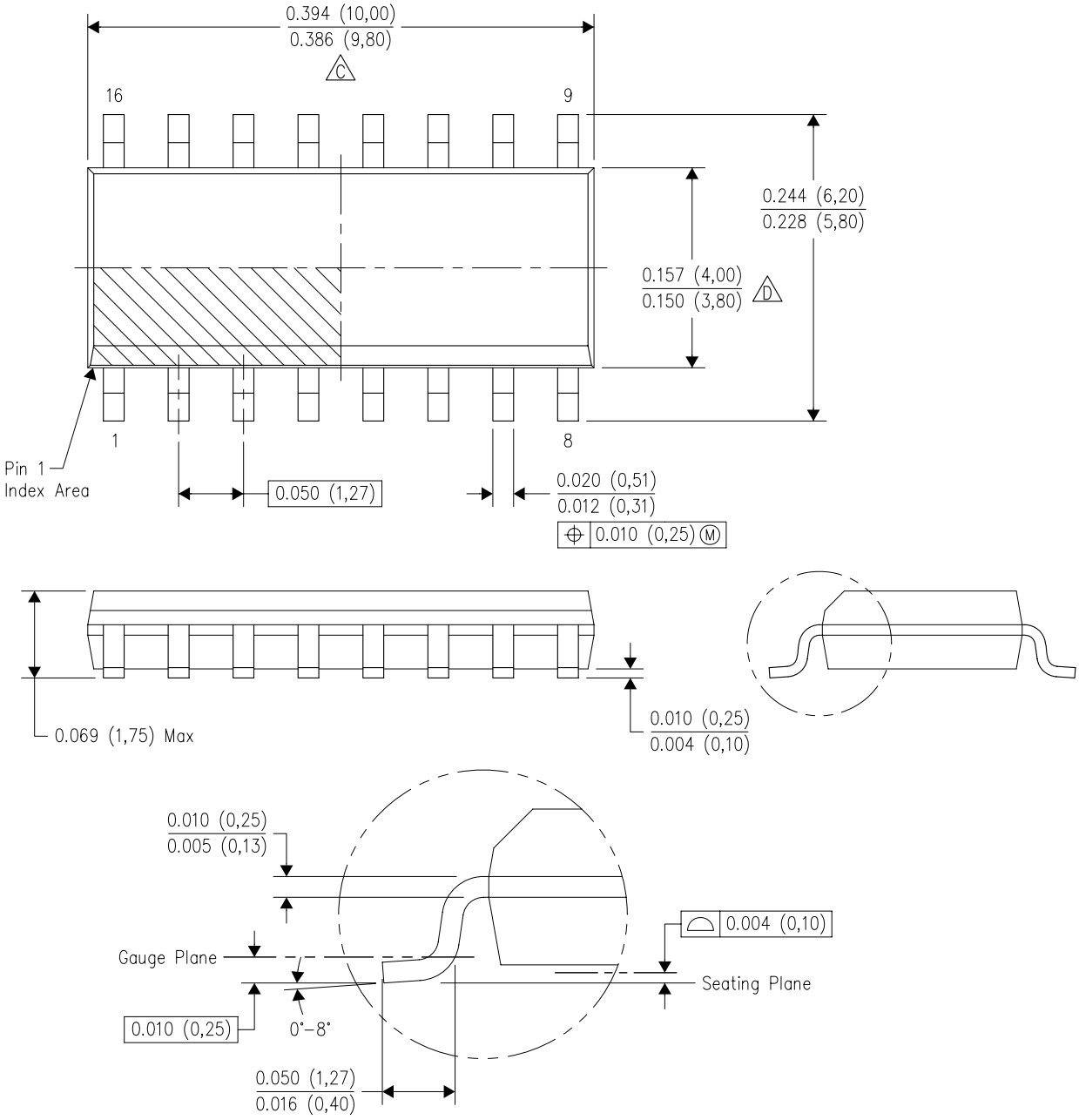
EXPOSED PAD 17
80% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE

4225140/A 07/2019

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

D (R–PDSO–G16) PLASTIC SMALL OUTLINE



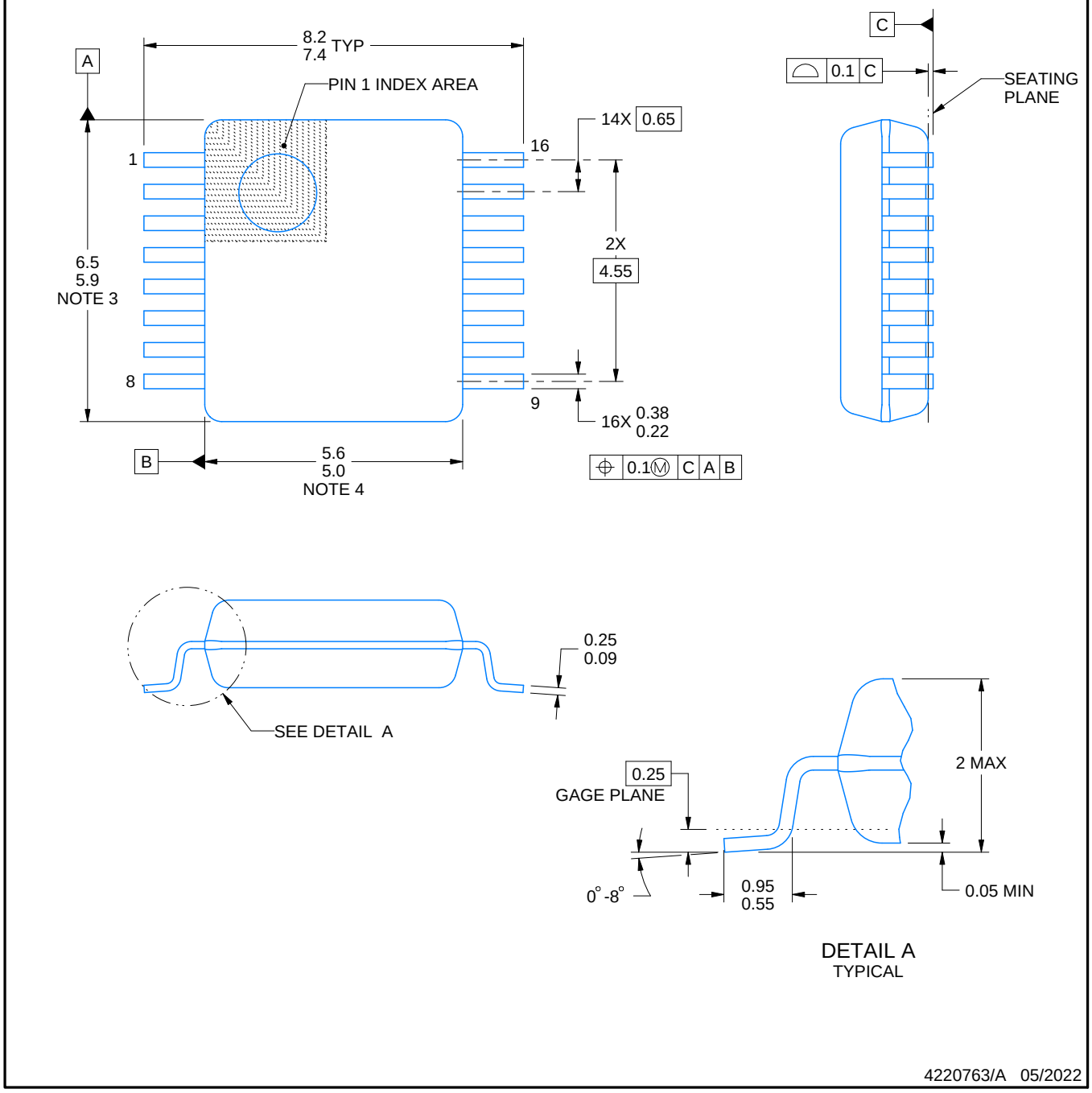
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AC.

PACKAGE OUTLINE

DB0016A

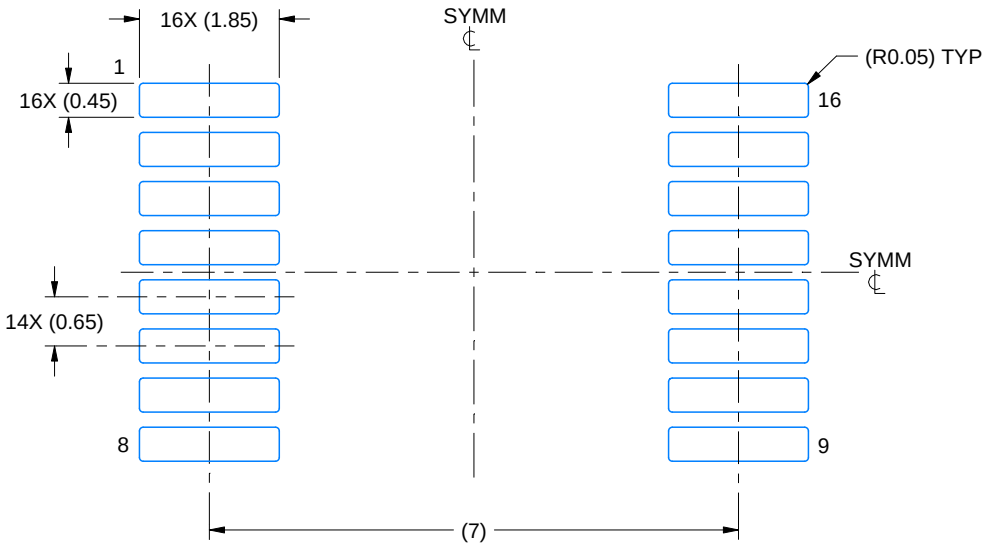
SSOP - 2 mm max height

SMALL OUTLINE PACKAGE

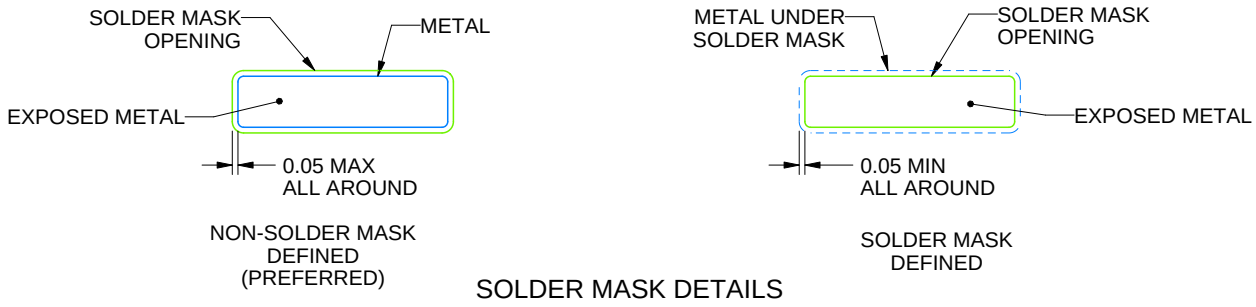


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-150.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

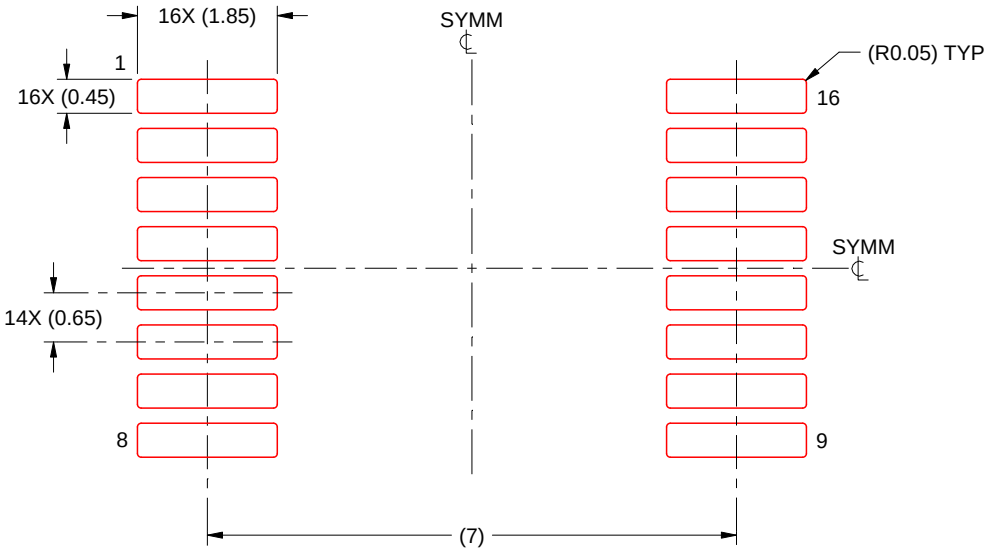


SOLDER MASK DETAILS

4220763/A 05/2022

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220763/A 05/2022

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

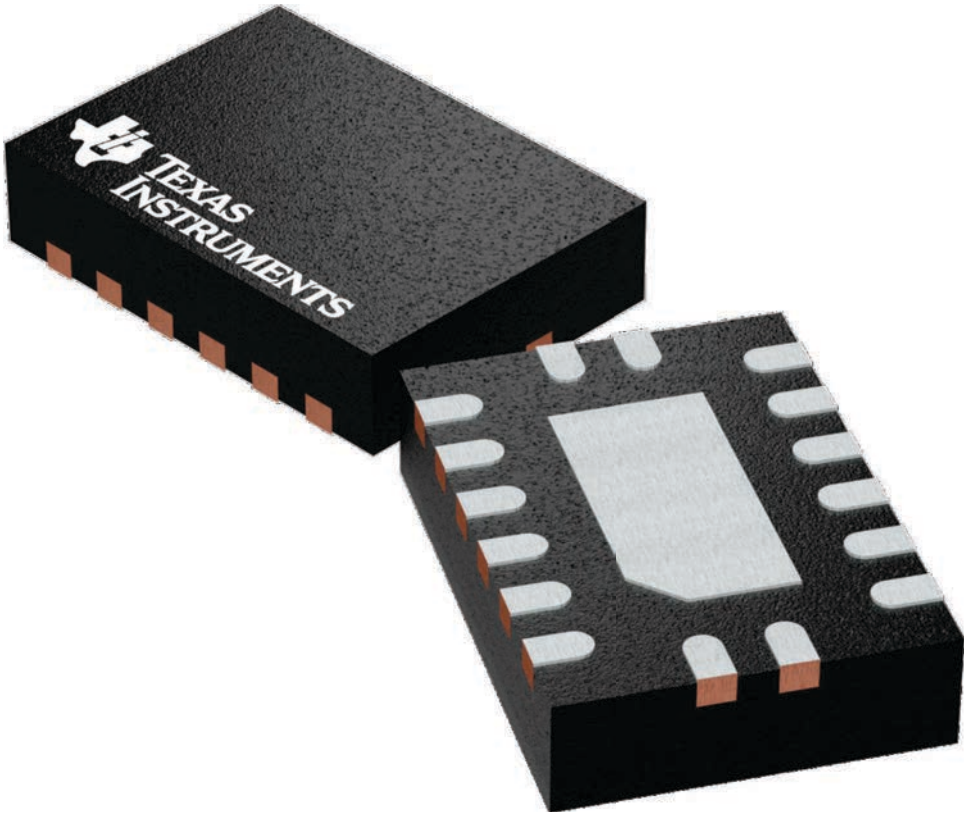
BQB 16

WQFN - 0.8 mm max height

2.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



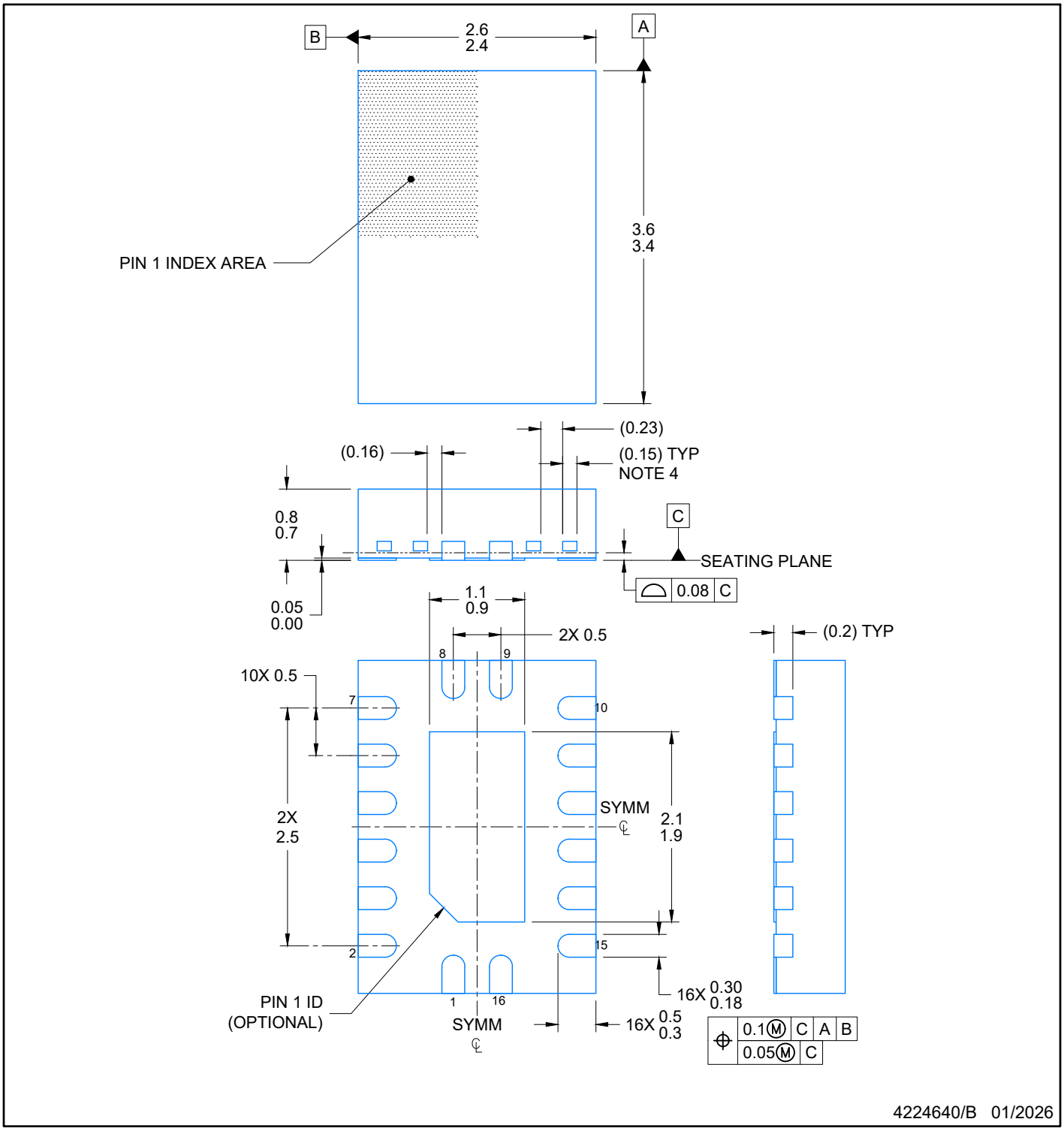
4226161/A

PACKAGE OUTLINE

BQB0016A

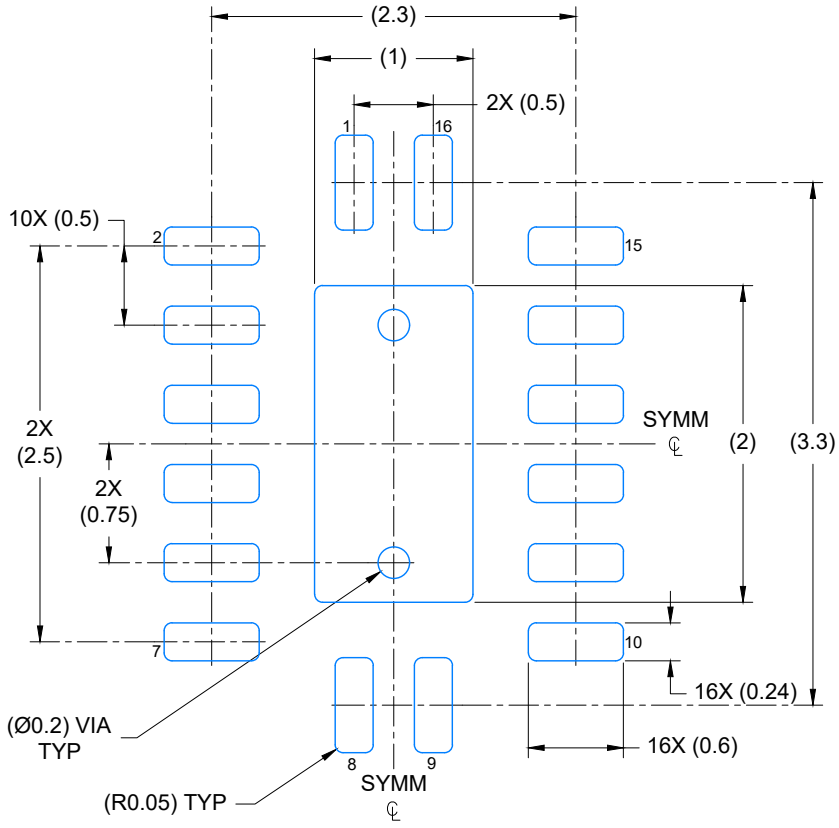
WQFN - 0.8 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD

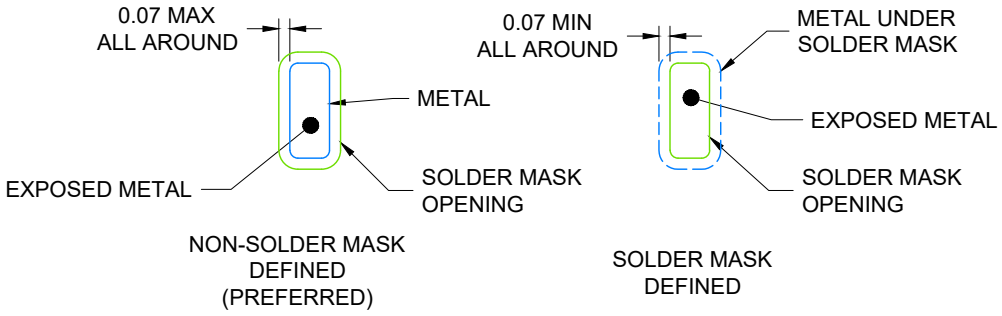


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.
4. Features may differ or may not be present



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

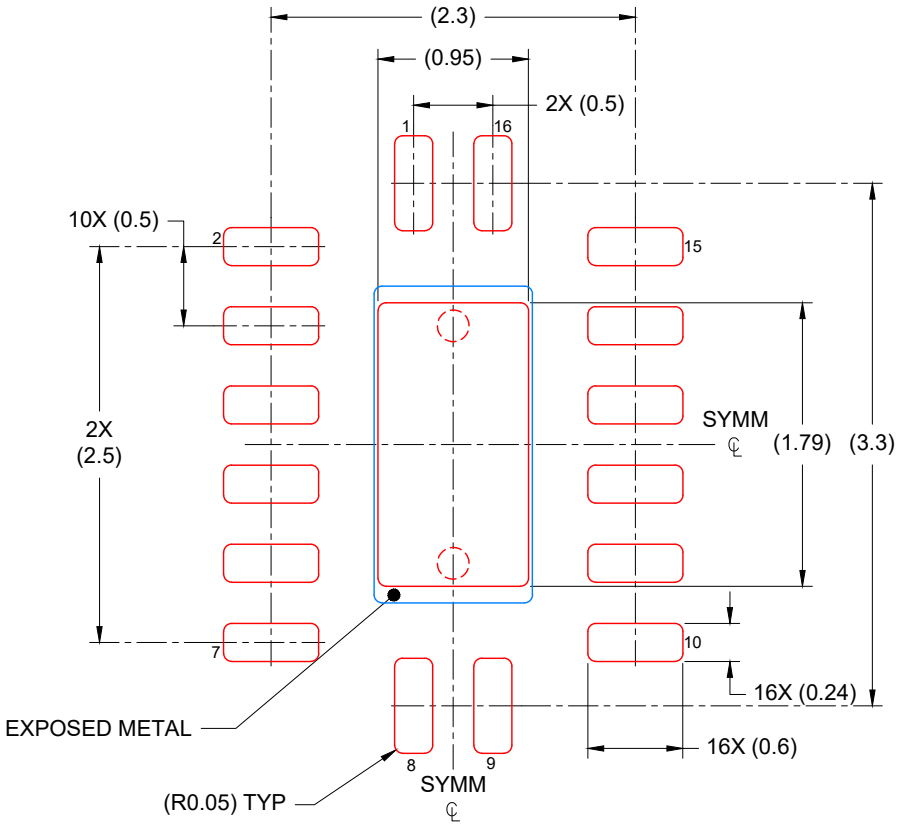


4224640/B 01/2026

1. NOTES: (continued)

5. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

6. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
85% PRINTED COVERAGE BY AREA
SCALE: 20X

4224640/B 01/2026

NOTES: (continued)

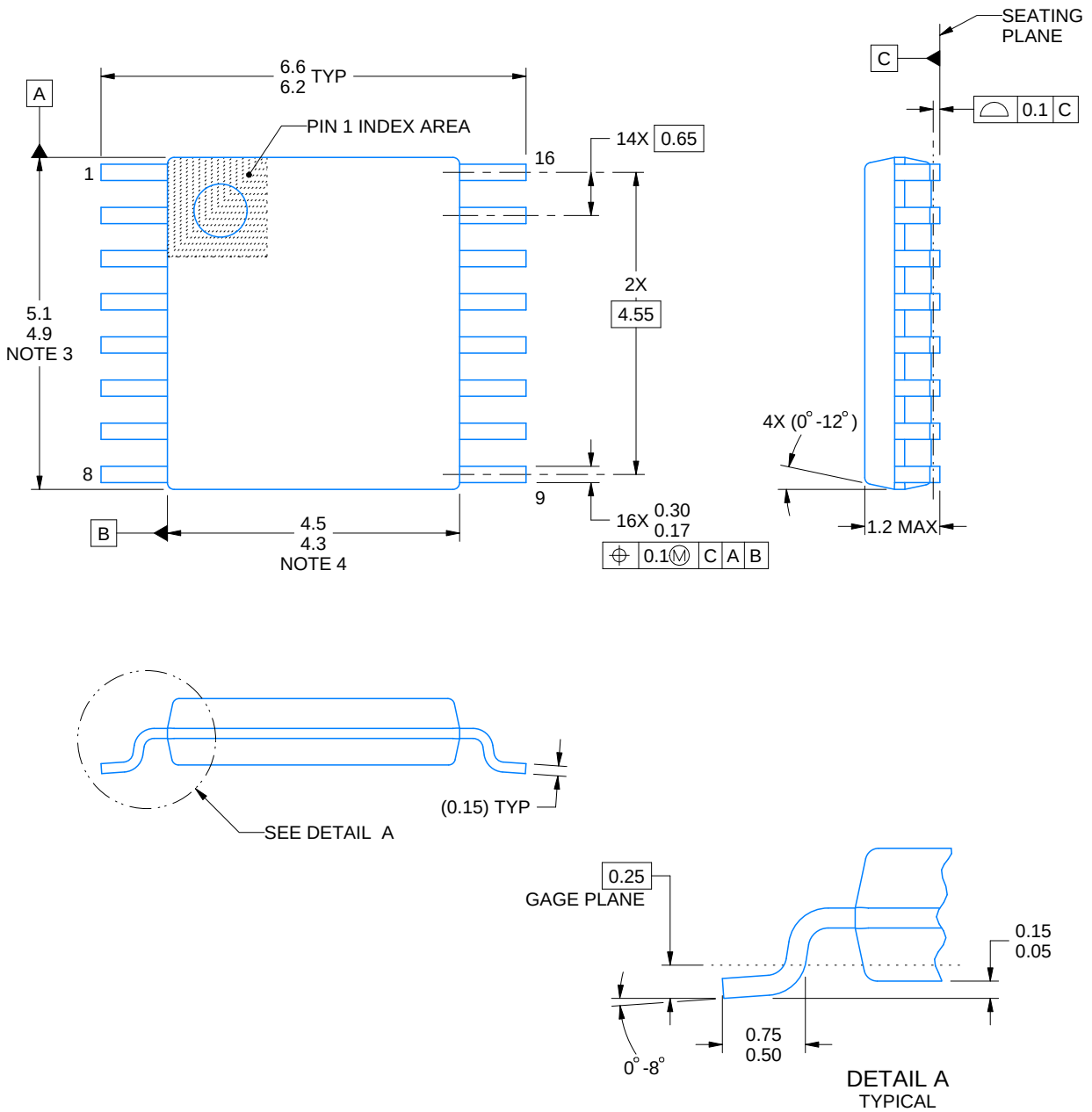
7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGE OUTLINE

PW0016A

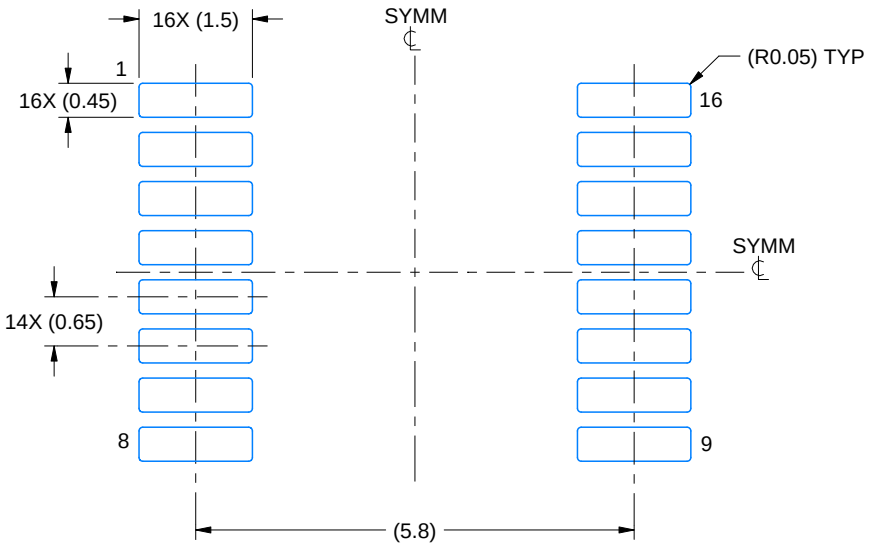
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

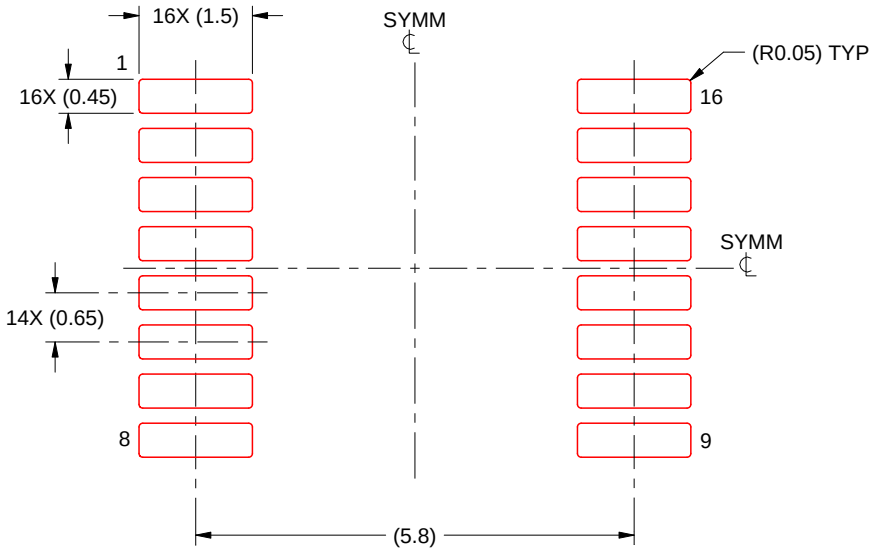


SOLDER MASK DETAILS

4220204/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

重要通知和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做出任何明示或暗示的担保，包括但不限于对适销性、与某特定用途的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他安全、安保法规或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的相关应用。严禁以其他方式对这些资源进行复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。对于因您对这些资源的使用而对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，您将全额赔偿，TI 对此概不负责。

TI 提供的产品受 TI 销售条款)、TI 通用质量指南 或 ti.com 上其他适用条款或 TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。 除非德州仪器 (TI) 明确将某产品指定为定制产品或客户特定产品，否则其产品均为按确定价格收入目录的标准通用器件。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

版权所有 © 2026，德州仪器 (TI) 公司

最后更新日期：2025 年 10 月